PNP BD132

SILICON PLANAR EPITAXIAL POWER TRANSISTORS

The BD132 are PNP transistors mounted in Jedec TO-126 plastic package.
Medium power applications.
PNP complements are BD131
Compliance to RoHS.

ABSOLUTE MAXIMUM RATINGS

Symbol	Ratings		Value	Unit
$-V_{CEO}$	Collector-Emitter Voltage		45	V
$-V_{CBO}$	Collector-Base Voltage		45	V
$-V_{EBO}$	Emitter-Base Voltage		4	V
I_C	Collector Current	$-I_C$	3	A
		$-I_{CM}$	6	
I_B	Base current (peak value)	$-I_{BM}$	0.5	A
	Reverse base current (peak value)	$-I_{BM}$	0.5	
P_T	Total power Dissipation	@ T_{mb} = 60℃	15	Watts
T_J	*Junction Temperature*		150	℃
T_{Stg}	Storage Temperature		-65 to +150	℃

THERMAL CHARACTERISTICS

Symbol	Ratings	Value	Unit
$R_{thJ\text{-}mb}$	Thermal Resistance, Junction to mouting base	6	K/W

ELECTRICAL CHARACTERISTICS

TC=25℃ unless otherwise noted

Symbol	Ratings	Test Condition(s)	Min	Typ	Max	Unit
$-I_{CBO}$	Collector cut-off current	I_E=0 , $-V_{CB}$=40 V	-	-	5	µA
		I_E=0 , $-V_{CB}$=40 V ,T_j= 150℃	-	-	500	
$-I_{EBO}$	Emitter cut-offcurrent	I_C=0, $-V_{EB}$=3 V	-	-	5	µA
$-V_{CE(SAT)}$	Collector-Emitter saturation Voltage	$-I_C$=0.5 A, $-I_B$=50 mA	-	-	0.3	V
		$-I_C$=2.0 A, $-I_B$=200 mA	-	-	1.2	
$-V_{BE(SAT)}$	Base-Emitter saturation Voltage	$-I_C$=0.5 A, $-I_B$=50 mA	-	-	0.7	V
		$-I_C$=2.0 A, $-I_B$=200 mA	-	-	1,5	
h_{FE}	DC Current Gain	$-V_{CE}$=12 V, $-I_C$=500m A	40	-	-	
		$-V_{CE}$=1 V, $-I_C$=2 A	20	-	-	

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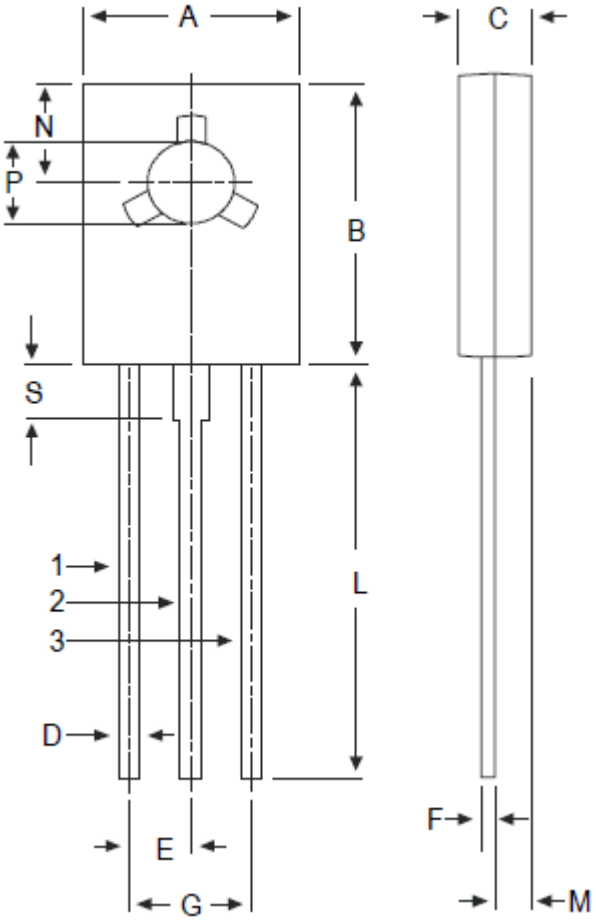
MECHANICAL DATA CASE TO-126

	DIMENSIONS	
	min	max
A	7.4	7.8
B	10.5	10.8
C	2.4	2.7
D	0.7	0.9
E	2.25 typ.	
F	0.49	0.75
G	4.4 typ.	
L	15.7 typ.	
M	1.27 typ.	
N	3.75 typ.	
P	3.0	3.2
S	2.54 typ.	



Pin 1 :	Emitter
Pin 2 :	Collector
Pin 3 :	Base

Revised September 2012

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